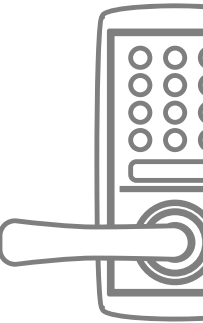
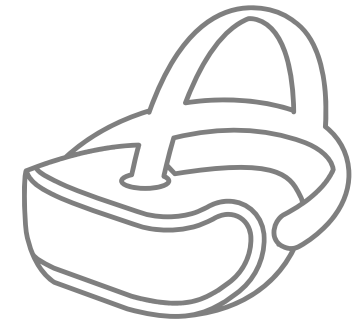
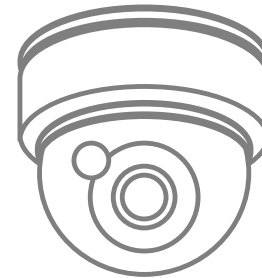
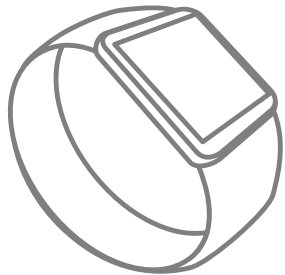
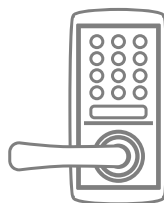


LED Lighting

Solution Proposal by Toshiba

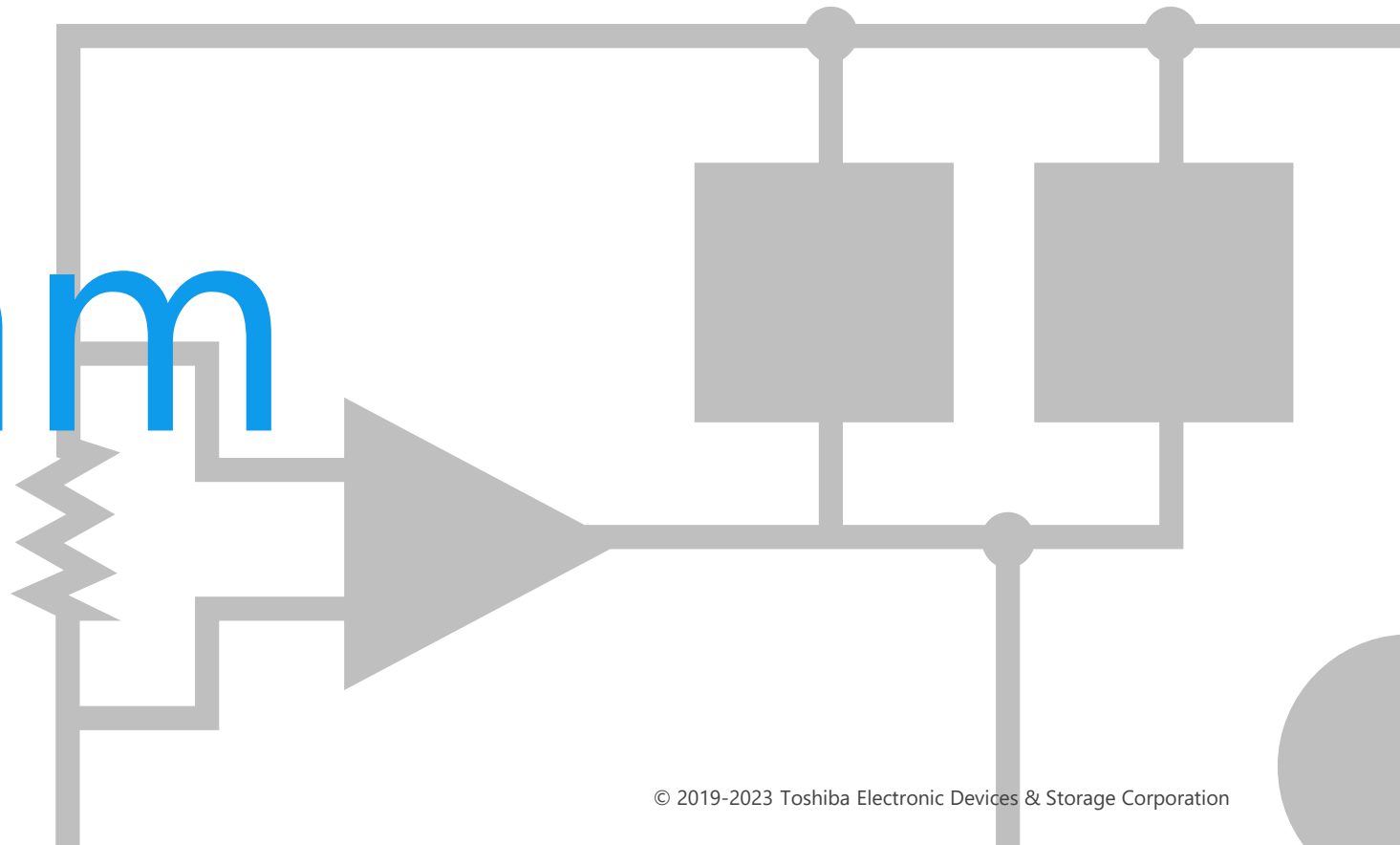




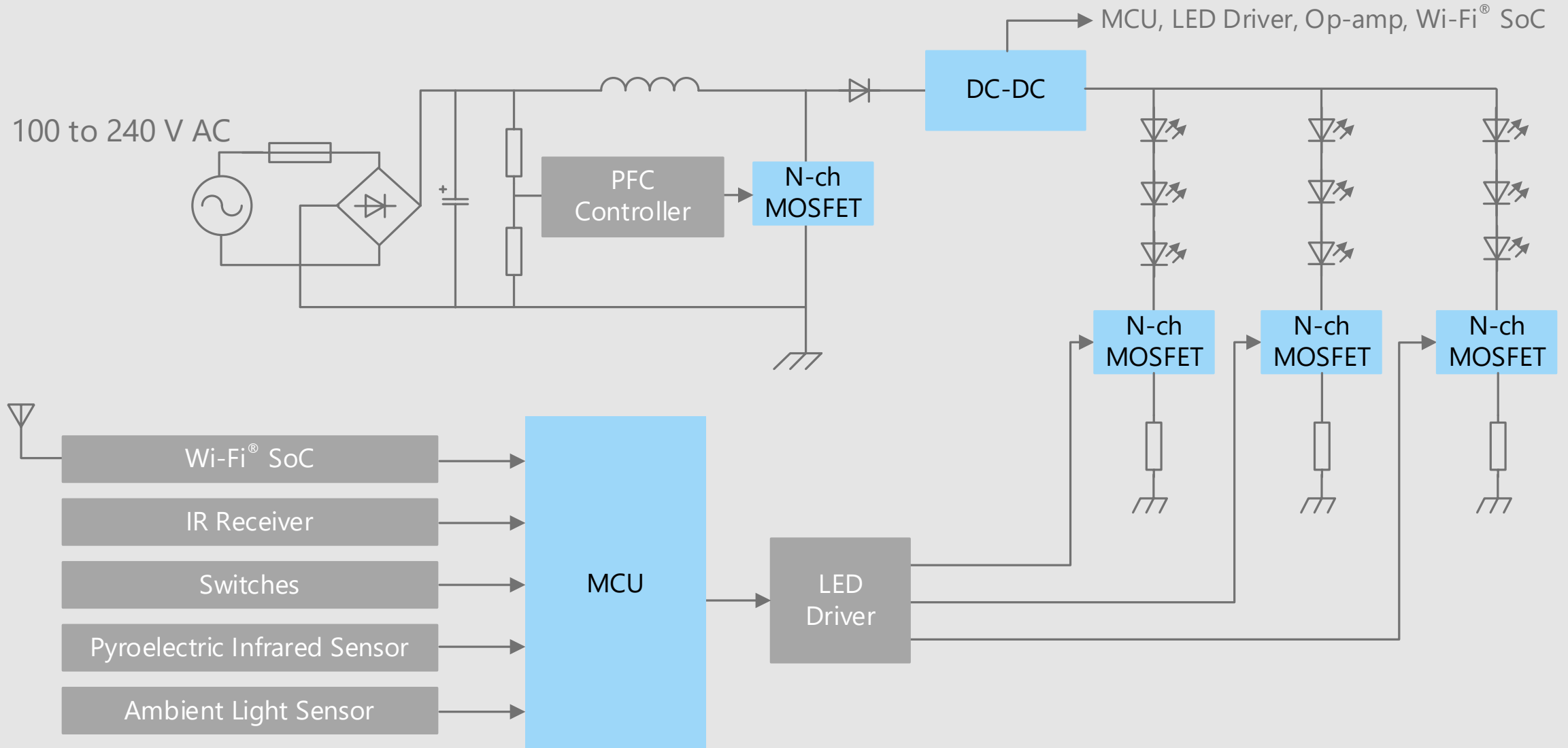
Toshiba Electronic Devices & Storage Corporation provides comprehensive device solutions to customers developing new products by applying its thorough understanding of the systems acquired through the analysis of basic product designs.



Block Diagram

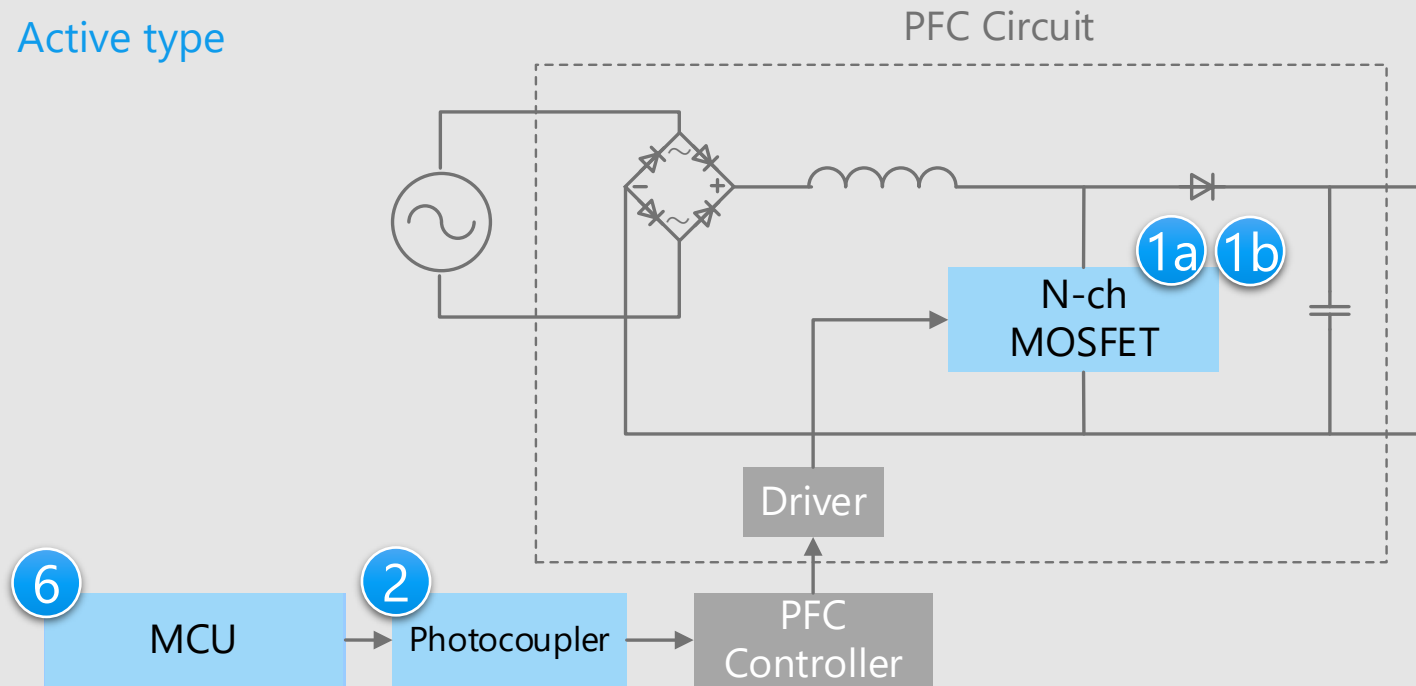


LED lighting Overall block diagram



PFC circuit

Active type



* Click on the number in the circuit diagram to jump to the detailed description page

Criteria for device selection

- MOSFET is suitable for active type PFC circuit.
- The transistor coupler is for signal isolation.
- MCU can be used for PFC control.

Proposals from Toshiba

- **Suitable for high efficiency power supply switching**
DTMOSVI Series MOSFET
SiC MOSFET
- **High current transfer ratio and high temperature operation have been achieved**
Transistor output photocoupler
- **Built-in analog input interface at low power consumption and efficient software development**
MCU M3H Group

1a

1b

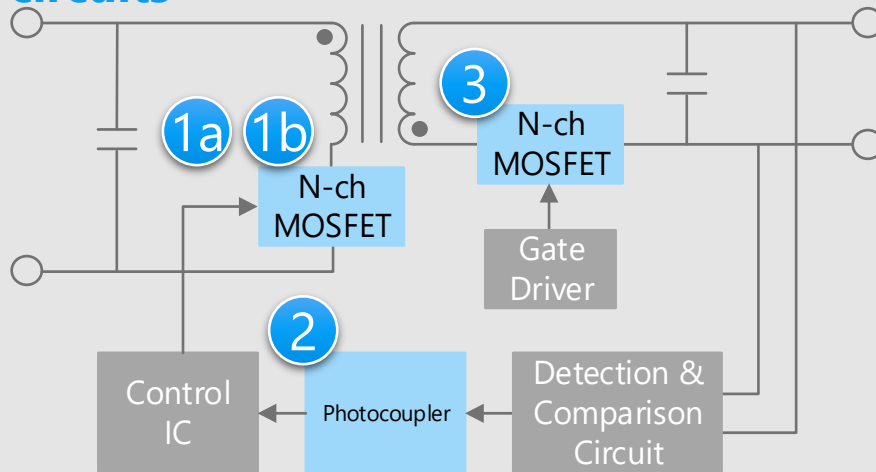
2

6

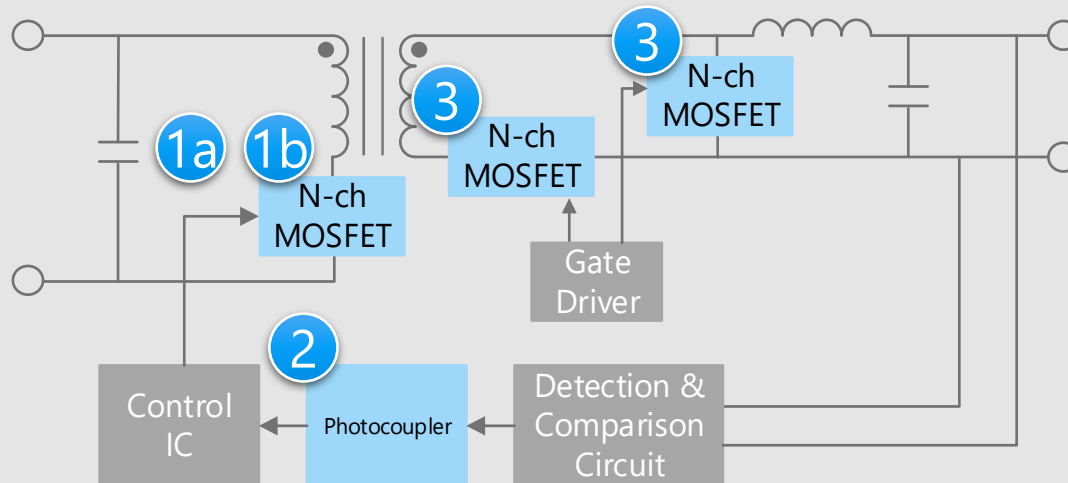
LED lighting Detail of power supply unit (2)

DC-DC converter circuits

Flyback type



Forward type



* Click on the number in the circuit diagram to jump to the detailed description page

Criteria for device selection

- By using a MOSFET with low on-resistance and high heat dissipation efficiency, a set having low heat generation and low power consumption is realized.
- The transistor coupler is for signal isolation.
- Small package products contribute to the reduction of circuit board area.

Proposals from Toshiba

- **Suitable for high efficiency power supply switching**
DTMOSVI Series MOSFET
SiC MOSFET
- **High current transfer ratio and high temperature operation have been achieved**
Transistor output photocoupler
- **MOSFET with low on-resistance and high heat dissipation efficiency**
U-MOS Series MOSFET

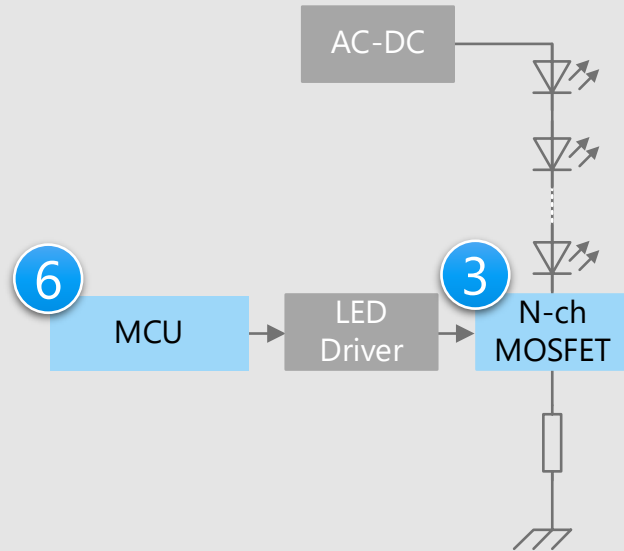
1a

1b

2

3

LED drive circuit



Criteria for device selection

- By using a MOSFET with low on-resistance and high heat dissipation efficiency, a set having low heat generation and low power consumption is realized.

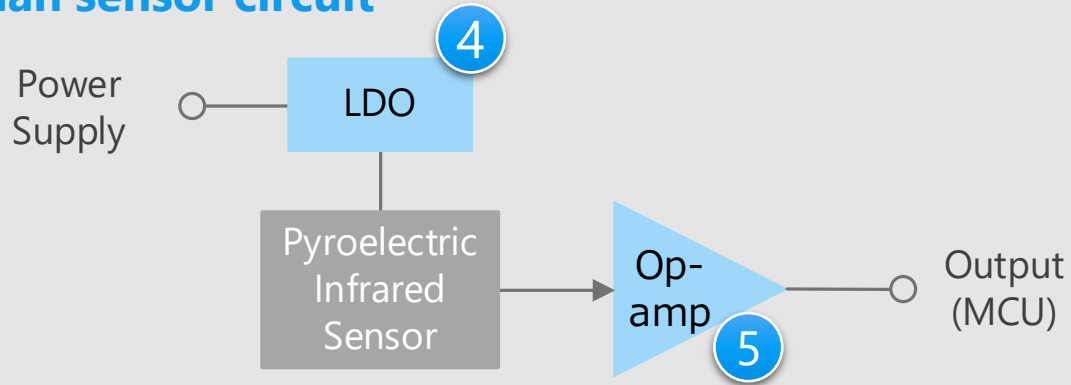
Proposals from Toshiba

- **MOSFET with low on-resistance and high heat dissipation efficiency**
U-MOS Series MOSFET (3)
- **Built-in analog input interface at low power consumption and efficient software development**
MCU M3H Group (6)

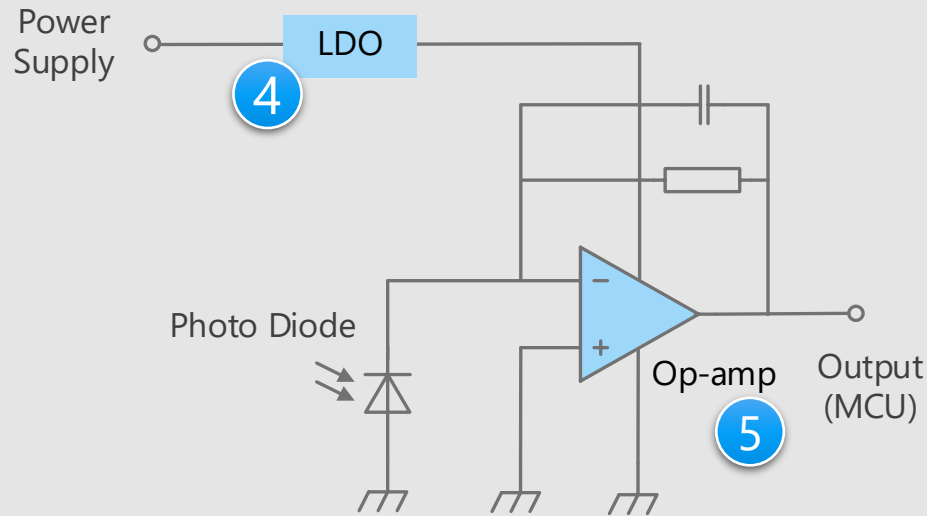
* [Click on the number in the circuit diagram to jump to the detailed description page](#)

LED lighting Detail of sensor signal input unit

Human sensor circuit



Ambient light sensor circuit



Criteria for device selection

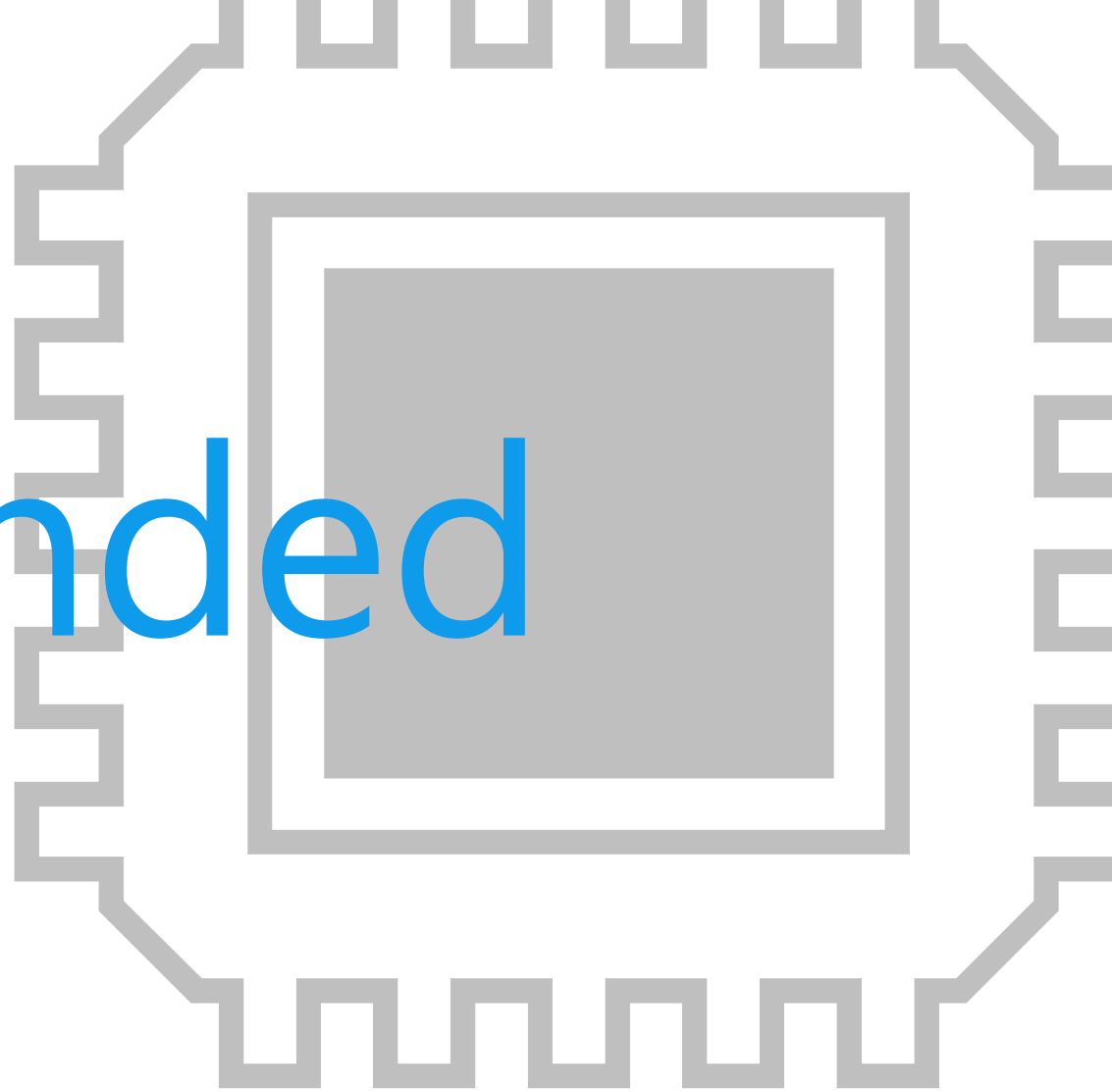
- PSRR (Power Supply Rejection Ratio) of LDO regulator is an important parameter for sensor modules.
- The operational amplifier should be low current consumption or low noise device.

Proposals from Toshiba

- **Supply the power with low noise**
Small surface mount LDO regulator 4
- **Amplification of detected very small signal with low noise**
Low current consumption op-amp / Low noise op-amp 5

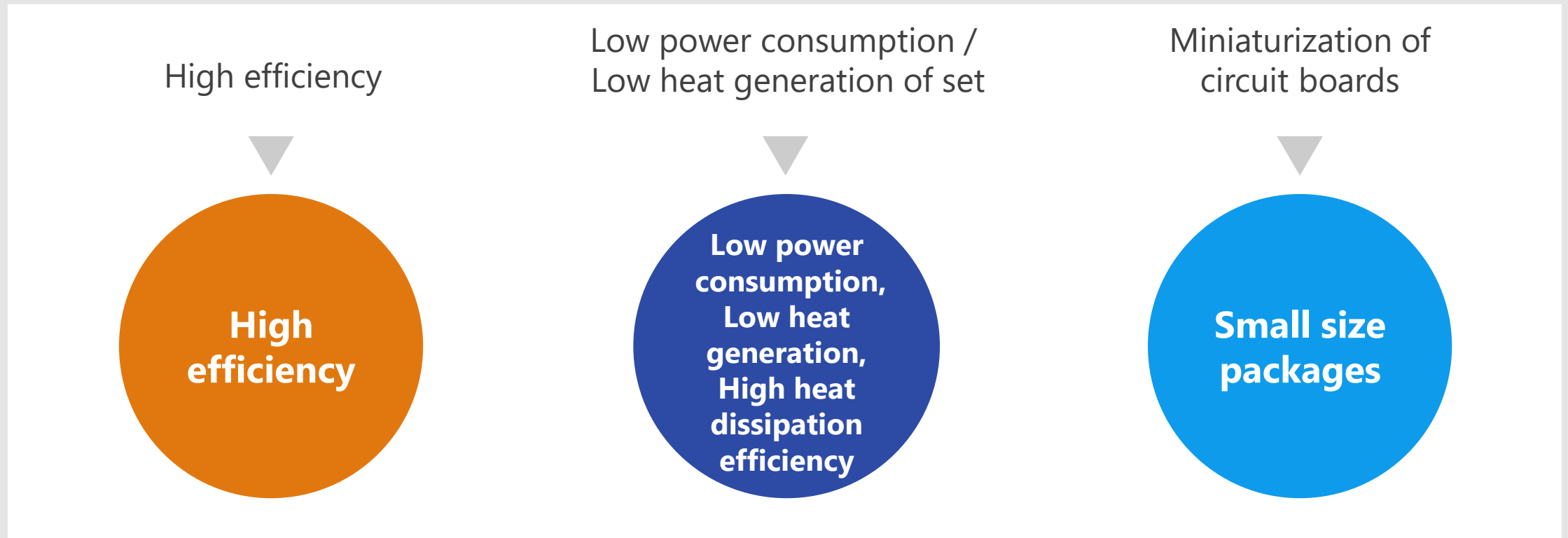
* Click on the blue circled numbers above to view detailed descriptions.

Recommended Devices



Device solutions to address customer needs

As described above, in the design of LED lighting, “**High efficiency**”, “**Low power consumption / Low heat generation of set**” and “**Miniaturization of circuit boards**” are important factors. Toshiba’s proposals are based on these three solution perspectives.



Device solutions to address customer needs

High efficiency

Low power consumption,
Low heat generation,
High heat dissipation efficiency

Small size packages

1a	DTMOSVI Series MOSFET	●	●	●
1b	SiC MOSFET	●	●	
2	Transistor output photocoupler			●
3	U-MOS Series MOSFET	●	●	●
4	Small surface mount LDO regulator	●	●	●
5	Low current consumption op-amp / Low noise op-amp			●
6	MCU M3H Group	●	●	●

Value provided

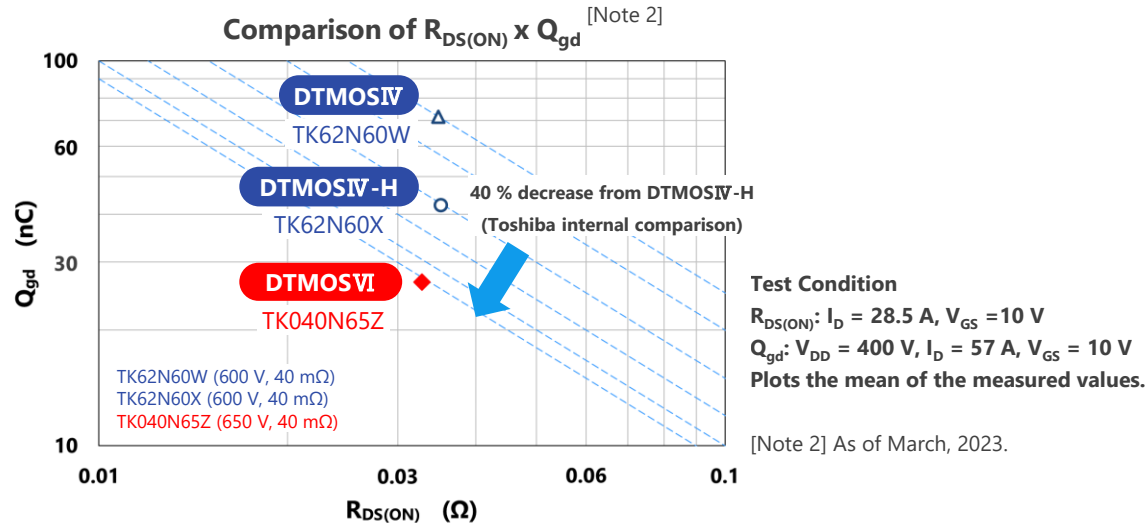
Realizes improvement of power supply efficiency by 40 % (comparison of Toshiba's conventional products) reduction of $R_{DS(ON)} \times Q_{gd}$

1 $R_{DS(ON)} \times Q_{gd}$ reduced by 40 %

Using a single epitaxial process, the figure of merit $R_{DS(ON)} \times Q_{gd}$ was reduced by 40 % by optimizing the structure (comparison of Toshiba's DTMOSIV-H 600 V products). By realizing low $R_{DS(ON)} \times Q_{gd}$, device switching loss was reduced contributing to improvement in power supply efficiency of equipment.



2 RonA reduced by 18 %

The figure of merit RonA of the latest generation [Note1] DTMOSVI has been reduced by 18 % compared with the previous generation (Toshiba's DTMOSVI 650 V products). Achieving low on-resistance while maintaining high voltage contributes to high efficiency of equipment.



[Note1] As of March, 2023

Lineup

Part number	TK065U65Z	TK040N65Z
Package	TOLL 	TO-247 
V_{DSS} [V]	650	650
I_D [A]	38	57
$R_{DS(ON)}$ [Ω] @ $V_{GS} = 10 \text{ V}$	Typ.	0.051
	Max	0.065
Polarity	N-ch	N-ch

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Value provided

The performance index $R_{DS(ON)} \times Q_{gd}$, which shows switching characteristics, is reduced by 80 % compared with Toshiba's existing products. This contributes to lower loss of power supply in application.

1 Low $R_{DS(ON)} \times Q_{gd}$

For the latest products, the performance index $R_{DS(ON)} \times Q_{gd}$, which shows the relation between conduction loss and switching loss, is reduced by 80 % compared with Toshiba's existing products by optimizing its cell structure.

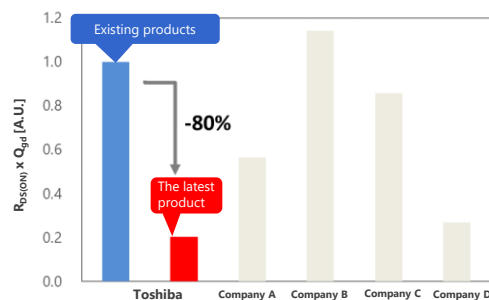
2 Wide V_{GSS} specification

The specification of the gate-source voltage is -10 to 25 V, which is wider than that of other companies' products, allows a wider margin for the drive voltage and makes gate drive design considering overshoot easier. (Recommended drive voltage: 18 V)

3 Built-in Schottky barrier diode

Built-in Schottky barrier diode reduces V_{DSF} during reverse conduction to 1.35 V (typ.). In addition, by energizing the Schottky barrier diode, fluctuation in $R_{DS(ON)}$ caused by the spread of defects is suppressed.

Comparison of $R_{DS(ON)} \times Q_{gd}$



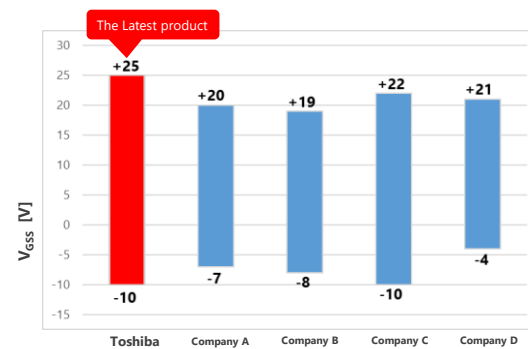
Measurement conditions

$R_{DS(ON)}$: $V_{GS} = 18 \text{ V}$, $I_D = 20 \text{ A}$, $T_a = 25 \text{ }^\circ\text{C}$

Q_{gd} : $V_{DD} = 800 \text{ V}$, $V_{GS} = 18 \text{ V}$, $I_D = 20 \text{ A}$, $T_a = 25 \text{ }^\circ\text{C}$



(Toshiba internal comparison, as of May 2022)

Comparison of V_{GSS} specification



(Toshiba internal comparison based on the datasheet of each company's 1200 V voltage products as of July 2023.)

Lineup

Part number	TW107N65C	TW140N120C	TW107Z65C	TW140Z120C
Package	TO-247 		TO-247-4L(X) 	
V_{DSS} [V]	650	1200	650	1200
I_D [A]	20	20	20	20
$R_{DS(ON)}$ [Ω] @ $V_{GS} = 18 \text{ V}$	Typ.	0.107	0.140	0.107
	Max	0.145	0.182	0.152
Polarity	N-ch	N-ch	N-ch	N-ch

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2 Transistor output photocoupler

TLP383 / TLP293 / TLP385

High efficiency

Low power consumption,
Low heat generation,
High heat dissipation efficiency

Small size packages

Value provided

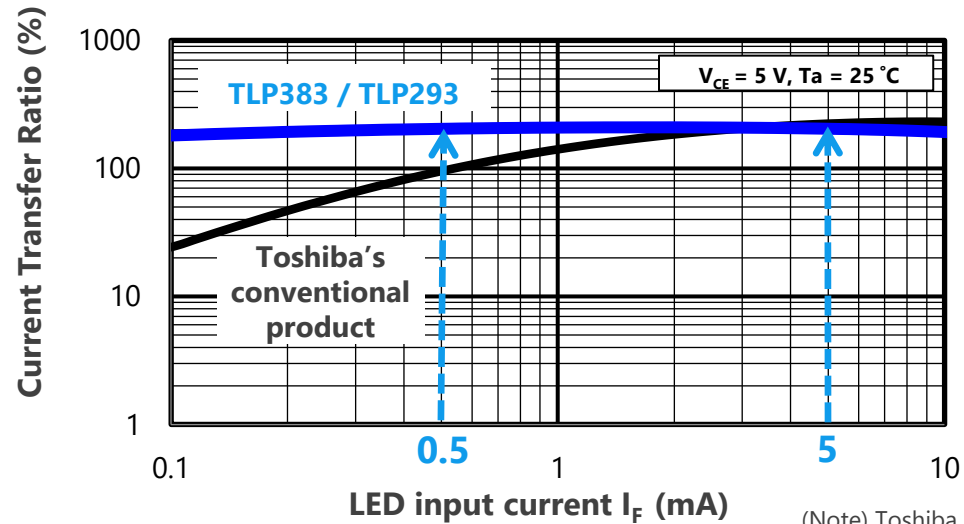
High CTR (Current Transfer Ratio) is realized even in low input current range ($I_F = 0.5 \text{ mA}$).

1 High current transfer ratio

The TLP383 and TLP293 are high isolation photocouplers that optically couple a phototransistor and high output infrared LED. Compared to Toshiba's conventional products (TLP385), higher CTR (Current Transfer Ratio) in low input current range (@ $I_F = 0.5 \text{ mA}$) is realized.




2 Designed for high temperature operation

The TLP383 and TLP293 are designed to operate even under severe ambient temperature conditions.



(Note) Toshiba internal comparison

Lineup

Part number	TLP383	TLP293	TLP385
Package	4pin SO6L 	SO4 	4pin SO6L 
BV_S [Vrms]	5000	3750	5000
T_{opr} [$^\circ\text{C}$]	-55 to 125	-55 to 125	-55 to 110

[Return to Block Diagram TOP](#)

Value provided

Contributes to lower heat generation of system by providing low on-resistance and a highly heat dissipation package (DSOP Advance).

1 Low $R_{DS(ON)}$ (on-resistance)

By keeping the $R_{DS(ON)}$ (drain-source on-resistance) low, heat build-up and power consumption can be reduced. Products are prepared from on-resistance of 0.36 m Ω (Typ.).

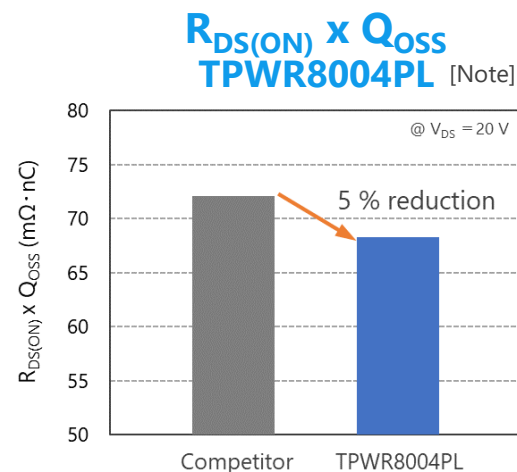
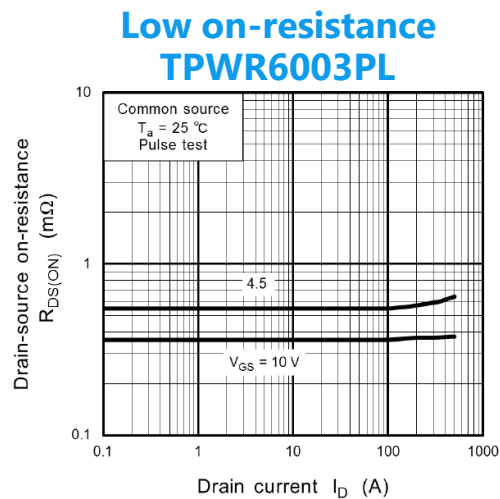
2 Small Q_{OSS}



Contributes low loss due to small Q_{OSS} . TPWR8004PL's performance index $R_{DS(ON)} \times Q_{OSS}$ is deducted to 5 % [Note] than competitor's products.

3 Variety of packages

Adding SOP Advance of industry standard package, DSOP Advance of double-side heat dissipation package on same footprint had been prepared. Packages can be selected according to the set.

[Note] Comparison with competitor's product with equivalent ratings. As of March, 2023. Based on Toshiba's measurement data.



Lineup					
Part number	TPWR6003PL	TPWR8004PL	TPHR7404PU	TPHR8504PL	
Package	DSOP Advance 		SOP Advance 		
V_{DSS} [V]	30	40	40	40	
I_D [A]	150 (412*)	150 (340*)	150 (400*)	150 (340*)	
$R_{DS(ON)}$ [m Ω] @ $V_{GS} = 10$ V	Typ.	0.36	0.65	0.51	0.7
	Max	0.6	0.8	0.74	0.85
Polarity	N-ch	N-ch	N-ch	N-ch	
Generation	U-MOSIX-H	U-MOSIX-H	U-MOSIX-H	U-MOSIX-H	

*: Silicon limit

[Return to Block Diagram TOP](#)

Value provided

Lineup of low on-resistance products is provided and improvement of trade-off between on-resistance and capacitance contribute to higher efficiency of power supply.

1 Fast switching speed

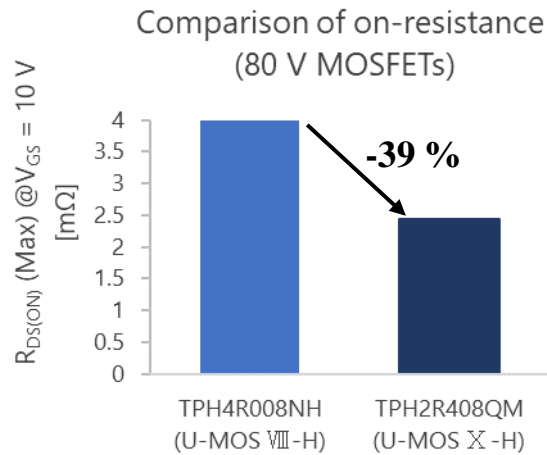
Reducing switching loss through high speed operation contributes to higher power supply efficiency.

2 Small gate input charge

Small gate input charge reduces the performance required for driving the MOSFET. It contributes to improving switching characteristics.




3 Low on-resistance

By reducing the on-resistance between the drain and source, heat generation and power consumption can be kept low.



[Note] Toshiba internal comparison

Lineup

Part number	TPH2R408QM	TPH4R008QM	TPN8R408QM	TPN12008QM	TPN19008QM	TK5R1P08QM	TK6R9P08QM
Package	SOP Advance(N) 	TSON Advance 		DPAK 			
V _{DSS} [V]	80	80	80	80	80	80	80
I _D [A]	120 (200*)	86 (140*)	32 (77*)	26 (60*)	34 (38*)	84 (105*)	62 (83*)
R _{DS(ON)} [mΩ] @V _{GS} = 10 V	Typ.	1.9	3.1	6.5	9.6	14.7	5.5
	Max	2.43	4	8.4	12.3	19	6.9
Polarity	N-ch	N-ch	N-ch	N-ch	N-ch	N-ch	N-ch
Generation	U-MOS X -H	U-MOS X -H	U-MOS X -H	U-MOS X -H	U-MOS X -H	U-MOS X -H	U-MOS X -H

*: Silicon limit

[Return to Block Diagram TOP](#)

Value provided

Wide lineup from general purpose type to small package type are provided.
Contribute to realize a stable power supply not affected by fluctuation of battery.

1 Low dropout voltage

The originally developed latest process significantly improved the dropout voltage characteristics.

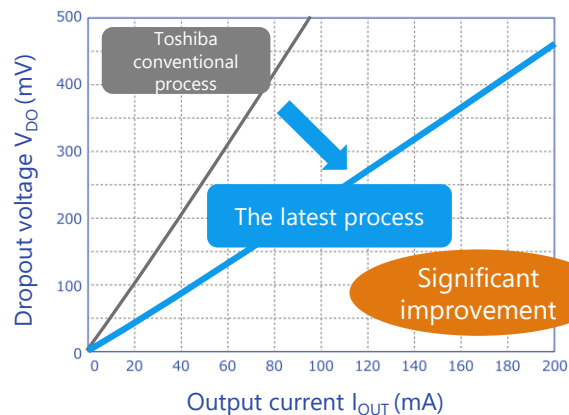
2 High PSRR Low output noise voltage

Many product series that realize both high PSRR (Power Supply Rejection Ratio) and low output noise voltage characteristics are provided. They are suitable for stable power supply for analog circuit.

3 Low current consumption

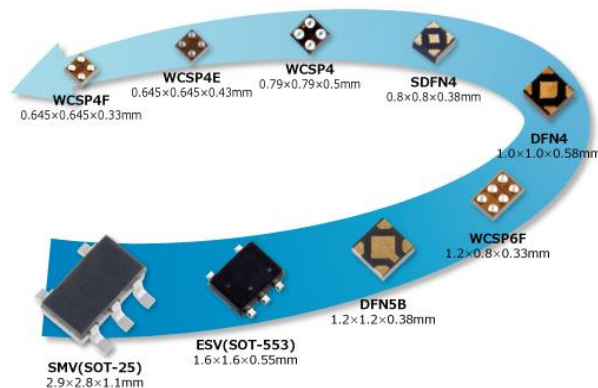
0.34 μA of $I_{B(ON)}$ is realized by utilizing CMOS process and unique circuit technology.
(TCR3U Series)

Low dropout voltage



(Note) Toshiba internal comparison

Rich package lineup



Lineup

Part number	TCR15AG Series	TCR13AG Series	TCR8BM Series	TCR5BM Series	TCR5RG Series	TCR3RM Series	TCR3U Series	TCR2L Series	TAR5 Series
Features	Low dropout voltage High PSRR				High PSRR Low noise Low current consumption		Low current consumption		15 V Input voltage Bipolar type
I_{OUT} (Max) [A]	1.5	1.3	0.8	0.5		0.3		0.2	
PSRR (Typ.) [dB] @f = 1 kHz	95	90	98	98	100	100	70	-	70
I_B (Typ.) [μA]	25	56	20	19	7	7	0.34	1	170

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5 Low current consumption op-amp / Low noise op-amp

TC75S102F / TC75S67TU

High efficiency

Low power consumption, Low heat generation, High heat dissipation efficiency

Small size packages

Value provided

Lineup includes low current consumption type that contributes to low power consumption and a low noise type that maximizes the performance of high performance sensors.

1 Low voltage operation

We have a lineup of low power supply voltage-driven operational amplifiers using CMOS process for low power supply voltage-driven wearable equipment.

2 Low current consumption (TC75S102F) $I_{DD} = 0.27 \text{ } [\mu\text{A}] \text{ (Typ.)}$

CMOS processes have been used to achieve lower current consumption. This contributes to lower power consumption and longer life of wearable equipment.

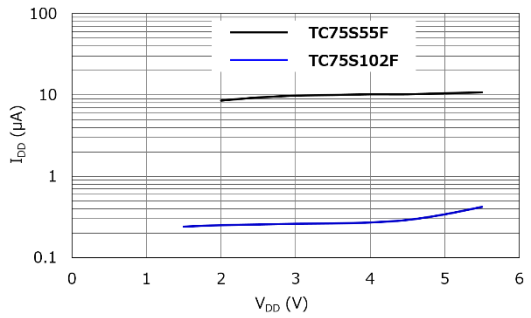
3 Low noise (TC75S67TU) $V_{NI} = 6.0 \text{ } [\text{nV}/\sqrt{\text{Hz}}] \text{ (Typ.) @ } f = 1 \text{ kHz}$

This CMOS operational amplifier can amplify minute signals detected by various sensors [Note] with very low noises. By optimizing the process, the equivalent input noise voltage has been reduced.

[Note] Sensor types: vibration, shock, acceleration, pressure, infrared, temperature, etc.

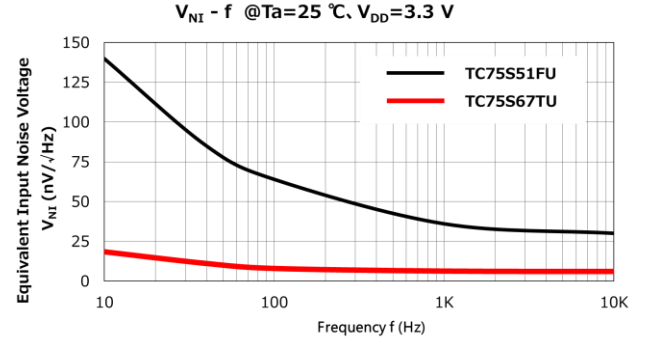
TC75S102F
Current Consumption Characteristic
(Toshiba internal comparison)

Low current consumption product TC75S102F





TC75S67TU
Noise Characteristic
(Toshiba internal comparison)

Reduce 1/f noise (10 Hz) by 86 % from our normal products



Lineup

Part number	TC75S102F	TC75S67TU
Package	SMV 	UFV 
$V_{DD} - V_{SS}$ [V]	1.5 to 5.5	2.2 to 5.5
V_{IO} (Max) [mV]	1.3	3
CMV_{IN} (Max) [V]	V_{DD}	1.4 (@ $V_{DD} = 2.5 \text{ V}$)
I_{DD} (Typ. / Max) [μA]	0.27 / 0.46 (@ $V_{DD} = 1.5 \text{ V}$)	430 / 700 (@ $V_{DD} = 2.5 \text{ V}$)
V_{NI} (Typ.) [$\text{nV}/\sqrt{\text{Hz}}$] @ $f = 1 \text{ kHz}$	-	6

[Return to Block Diagram TOP](#)

Value provided

Built-in 50 % duty control function in UART, compatible with Home Bus System (HBS).

1 Built-in Arm® Cortex®-M3 CPU core

The product lineup is equipped with Arm Cortex-M3 core (maximum operation frequency of 120 MHz). Various development tool and their partners allow users many options.

2 Compatible with HBS

UART function is equipped with 50 % duty control function and is compatible with HBS. A control system composed of HBS can be easily constructed using centralized management systems or thermostats.

3 Small package, low power consumption

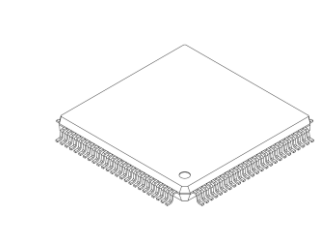
Several low power modes are available to support low power consumption. Package lineup of LQFP144 from small LQFP64 is provided.

TMPM3HQF*AFG



P-LQFP144-2020-0.50-002

TMPM3HNF*AFG



P-LQFP100-1414-0.50-002

TMPM3HLF*AUG



P-LQFP64-1010-0.50-003

Lineup			
Part number	TMPM3HQFD/Z/YAFG	TMPM3HNFD/Z/YAFG TMPM3HNFD/Z/YADFG	TMPM3HLFD/Z/YAUG
Operation frequency	120 MHz (Max)		
Code flash	512/384/256 KB		
RAM	66 KB (with parity)		
Timer	32bit x 8ch (16bit x 16ch)		
AD converter	21ch (12bit)	17ch (12bit)	12ch (12bit)
Serial communication	UART: 8ch, I ² C: 4ch, TSPI: 5ch	UART: 8ch, I ² C: 3ch, TSPI: 4ch	UART: 7ch, I ² C: 2ch, TSPI: 1ch
Package	P-LQFP144-2020-0.50-002	P-LQFP100-1414-0.50-002 P-QFP100-1420-0.65-003	P-LQFP64-1010-0.50-003

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